

## TO-92 Plastic-Encapsulated Transistors

### 2SA608N TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 0.5 \text{ W (Tamb=25°C)}$$

Collector current

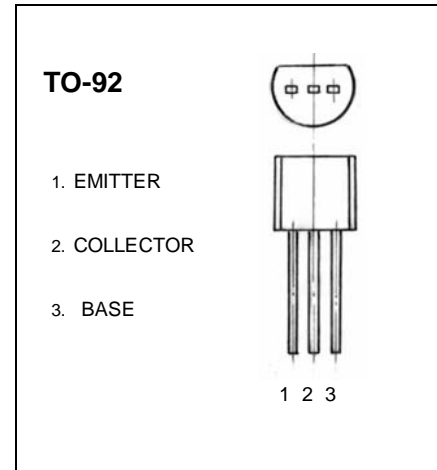
$$I_{CM} : -0.15 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -6V, I_C = -1mA$	160		560	
	$h_{FE(2)}$	$V_{CE} = -6V, I_C = -0.1mA$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_C = -10mA$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6V, I_E = 0, f = 1MHz$		3		pF

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	F	G
Range	160-320	280-560
Marking		